Roy G Gordon

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

275 papers	22,469 citations	76 h-index	144 g-index
293 ext. papers	24,534 ext. citations	7.6 avg, IF	7 L-index

#	Paper	IF	Citations
275	Anthraquinone Flow Battery Reactants with Nonhydrolyzable Water-Solubilizing Chains Introduced via a Generic Cross-Coupling Method. *ACS Energy Letters*, **2022**, 7, 226-235	20.1	5
274	Low energy carbon capture via electrochemically induced pH swing with electrochemical rebalancing.. *Nature Communications*, **2022**, 13, 2140	17.4	2
273	High-performance anthraquinone with potentially low cost for aqueous redox flow batteries. *Journal of Materials Chemistry A*, **2021**, 9, 26709-26716	13	7
272	Study of the crystal structure of SnS thin films by atomic layer deposition. *AIP Advances*, **2021**, 11, 035144	1.5	4
271	Functioning Water-Insoluble Ferrocenes for Aqueous Organic Flow Battery via Host-Guest Inclusion. *ChemSusChem*, **2021**, 14, 745-752	8.3	11
270	Chemical Vapor Deposition of Transparent, p-Type Cuprous Bromide Thin Films. *Chemistry of Materials*, **2021**, 33, 1426-1434	9.6	3
269	ALD Growth of MgxCa1□O on GaN and Its Band Offset Analysis. *ACS Applied Electronic Materials*, **2021**, 3, 845-853	4	
268	Extremely Stable Anthraquinone Negolytes Synthesized from Common Precursors. *CheM*, **2020**, 6, 1432-1442	16.2	43
267	Epitaxial growth of MgxCa1□O on 4H□SiC(0001) and □Ga2O3(left({bar 201} right)) wide band gap semiconductors with atomic layer deposition. *Journal of Materials Research*, **2020**, 35, 831-839	2.5	
266	Atomic layer deposition of cubic tin□alcium sulfide alloy films. *Journal of Materials Research*, **2020**, 35, 795-803	2.5	0
265	Effect of Molecular Structure of Quinones and Carbon Electrode Surfaces on the Interfacial Electron Transfer Process. *ACS Applied Energy Materials*, **2020**, 3, 1933-1943	6.1	17
264	In situ electrosynthesis of anthraquinone electrolytes in aqueous flow batteries. *Green Chemistry*, **2020**, 22, 6084-6092	10	12
263	pH swing cycle for CO2 capture electrochemically driven through proton-coupled electron transfer. *Energy and Environmental Science*, **2020**, 13, 3706-3722	35.4	27
262	Near Neutral pH Redox Flow Battery with Low Permeability and Long-Lifetime Phosphonated Viologen Active Species. *Advanced Energy Materials*, **2020**, 10, 2000100	21.8	51
261	Electrostatically Doped Silicon Nanowire Arrays for Multispectral Photodetectors. *ACS Nano*, **2019**, 13, 11717-11725	16.7	12
260	Strong, Long, Electrically Conductive and Insulated Coaxial Nanocables. *ACS Applied Polymer Materials*, **2019**, 1, 1717-1723	4.3	3
259	Atomic layer deposition of energy band tunable tin germanium oxide electron transport layer for the SnS-based solar cells with 400 mV open-circuit voltage. *Applied Physics Letters*, **2019**, 114, 213901	3.4	13

258	Symmetric All-Quinone Aqueous Battery. *ACS Applied Energy Materials*, **2019**, 2, 4016-4021	6.1	44
257	Enhancement of the open circuit voltage of Cu2O/Ga2O3 heterojunction solar cells through the mitigation of interfacial recombination. *AIP Advances*, **2019**, 9, 055203	1.5	16
256	A Water-Miscible Quinone Flow Battery with High Volumetric Capacity and Energy Density. *ACS Energy Letters*, **2019**, 4, 1342-1348	20.1	87
255	Mapping the frontiers of quinone stability in aqueous media: implications for organic aqueous redox flow batteries. *Journal of Materials Chemistry A*, **2019**, 7, 12833-12841	13	78
254	A Long-Lifetime All-Organic Aqueous Flow Battery Utilizing TMAP-TEMPO Radical. *CheM*, **2019**, 5, 1861-1870	18.2	94
253	A High Voltage Aqueous Zinc–Organic Hybrid Flow Battery. *Advanced Energy Materials*, **2019**, 9, 1900694	21.8	56
252	Synthesis of volatile, reactive coinage metal 5,5-bicyclic amidinates with enhanced thermal stability for chemical vapor deposition. *Dalton Transactions*, **2019**, 48, 6709-6713	4.3	4
251	Extending the Lifetime of Organic Flow Batteries via Redox State Management. *Journal of the American Chemical Society*, **2019**, 141, 8014-8019	16.4	93
250	A Phosphonate-Functionalized Quinone Redox Flow Battery at Near-Neutral pH with Record Capacity Retention Rate. *Advanced Energy Materials*, **2019**, 9, 1900039	21.8	122
249	Molecular Engineering of an Alkaline Naphthoquinone Flow Battery. *ACS Energy Letters*, **2019**, 4, 1880-1887	18.1	52
248	Band-Offset Analysis of Atomic Layer Deposition LaO on GaAs(111), (110), and (100) Surfaces for Epitaxial Growth. *ACS Applied Materials & Interfaces*, **2019**, 11, 28515-28519	9.5	5
247	A Long Lifetime Aqueous Organic Solar Flow Battery. *Advanced Energy Materials*, **2019**, 9, 1900918	21.8	23
246	Low Temperature Chemical Vapor Deposition of Cuprous Oxide Thin Films Using a Copper(I) Amidinate Precursor. *ACS Applied Energy Materials*, **2019**, 2, 7750-7756	6.1	11
245	Atomic Layer Deposition of Tin Monosulfide Using Vapor from Liquid Bis(,Pdiisopropylformamidinato)tin(II) and HS. *ACS Applied Materials & Interfaces*, **2019**, 11, 45892-45902	9.5	8
244	Non-corrosive, low-toxicity gel-based microbattery from organic and organometallic molecules. *Journal of Materials Chemistry A*, **2019**, 7, 24784-24787	13	6
243	Total-Ionizing-Dose Responses of GaN-Based HEMTs With Different Channel Thicknesses and MOSHEMTs With Epitaxial MgCaO as Gate Dielectric. *IEEE Transactions on Nuclear Science*, **2018**, 65, 46-52	1.7	9
242	Flow Batteries: Alkaline Benzoquinone Aqueous Flow Battery for Large-Scale Storage of Electrical Energy (Adv. Energy Mater. 8/2018). *Advanced Energy Materials*, **2018**, 8, 1870034	21.8	15
241	Alkaline Quinone Flow Battery with Long Lifetime at pH 12. *Joule*, **2018**, 2, 1894-1906	27.8	175

240	Obtaining a Low and Wide Atomic Layer Deposition Window (150-275 °C) for In O Films Using an In Amidinate and H O. *Chemistry - A European Journal*, **2018**, 24, 9525-9529	4.8	18
239	Alkaline Benzoquinone Aqueous Flow Battery for Large-Scale Storage of Electrical Energy. *Advanced Energy Materials*, **2018**, 8, 1702056	21.8	113
238	Alkaline Quinone Flow Battery with Long Lifetime at pH 12. *Joule*, **2018**, 2, 1907-1908	27.8	26
237	Vapor Deposition of Transparent, p-Type Cuprous Iodide Via a Two-Step Conversion Process. *ACS Applied Energy Materials*, **2018**, 1, 6953-6963	6.1	5
236	Total Ionizing Dose (TID) Effects in GaAs MOSFETs With La-Based Epitaxial Gate Dielectrics. *IEEE Transactions on Nuclear Science*, **2017**, 64, 164-169	1.7	3
235	Comparison of Capacity Retention Rates During Cycling of Quinone-Bromide Flow Batteries. *MRS Advances*, **2017**, 2, 431-438	0.7	9
234	A Neutral pH Aqueous Organic□Organometallic Redox Flow Battery with Extremely High Capacity Retention. *ACS Energy Letters*, **2017**, 2, 639-644	20.1	273
233	Quantitative Evaluation of Cobalt Disilicide/Si Interfacial Roughness. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P345-P349	2	1
232	Pure and conformal CVD nickel and nickel monosilicide in high-aspect-ratio structures analyzed by atom probe tomography. *Journal of Applied Physics*, **2017**, 121, 175301	2.5	1
231	Novel phase diagram behavior and materials design in heterostructural semiconductor alloys. *Science Advances*, **2017**, 3, e1700270	14.3	37
230	Synthesis of 5,5-Bicyclic Amidines as Ligands for Thermally Stable Vapor Deposition Precursors. *Organometallics*, **2017**, 36, 1453-1456	3.8	11
229	Direct-Liquid-Evaporation Chemical Vapor Deposition of Nanocrystalline Cobalt Metal for Nanoscale Copper Interconnect Encapsulation. *ACS Applied Materials & Interfaces*, **2017**, 9, 10914-10920	8.5	13
228	Vapor deposition of copper(I) bromide films via a two-step conversion process. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2017**, 35, 01B109	2.9	7
227	Anthraquinone Derivatives in Aqueous Flow Batteries. *Advanced Energy Materials*, **2017**, 7, 1601488	21.8	141
226	Measurement of contact resistivity at metal-tin sulfide (SnS) interfaces. *Journal of Applied Physics*, **2017**, 122, 045303	2.5	5
225	Enhancement-Mode AlGaN/GaN Fin-MOSHEMTs on Si Substrate With Atomic Layer Epitaxy MgCaO. *IEEE Electron Device Letters*, **2017**, 38, 1294-1297	4.4	15
224	UV-Vis spectrophotometry of quinone flow battery electrolyte for in situ monitoring and improved electrochemical modeling of potential and quinhydrone formation. *Physical Chemistry Chemical Physics*, **2017**, 19, 31684-31691	3.6	35
223	DC and RF Performance of AlGaN/GaN/SiC MOSHEMTs With Deep Sub-Micron T-Gates and Atomic Layer Epitaxy MgCaO as Gate Dielectric. *IEEE Electron Device Letters*, **2017**, 38, 1409-1412	4.4	13

222	Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. *Angewandte Chemie - International Edition*, **2016**, 55, 10228-33	16.4	24
221	A redox-flow battery with an alloxazine-based organic electrolyte. *Nature Energy*, **2016**, 1,	62.3	307
220	Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. *Angewandte Chemie*, **2016**, 128, 10384-10389	3.6	4
219	High-Performance InAlN/GaN MOSHEMTs Enabled by Atomic Layer Epitaxy MgCaO as Gate Dielectric. *IEEE Electron Device Letters*, **2016**, 37, 556-559	4.4	34
218	Epitaxial Growth of MgCaO on GaN by Atomic Layer Deposition. *Nano Letters*, **2016**, 16, 7650-7654	11.5	26
217	Transient terahertz photoconductivity measurements of minority-carrier lifetime in tin sulfide thin films: Advanced metrology for an early stage photovoltaic material. *Journal of Applied Physics*, **2016** , 119, 035101	2.5	39
216	Device engineering towards improved tin sulfide solar cell performance and performance reproducibility **2016**,		1
215	The impact of sodium contamination in tin sulfide thin-film solar cells. *APL Materials*, **2016**, 4, 026103	5.7	20
214	Synthetic and Spectroscopic Study of the Mechanism of Atomic Layer Deposition of Tin Dioxide. *Organometallics*, **2016**, 35, 1202-1208	3.8	9
213	A Two-Step Absorber Deposition Approach To Overcome Shunt Losses in Thin-Film Solar Cells: Using Tin Sulfide as a Proof-of-Concept Material System. *ACS Applied Materials & Interfaces*, **2016**, 8, 22664-70	9.5	19
212	Alkaline quinone flow battery. *Science*, **2015**, 349, 1529-32	33.3	622
211	Inversion-mode GaAs wave-shaped field-effect transistor on GaAs (100) substrate. *Applied Physics Letters*, **2015**, 106, 073506	3.4	4
210	Framework to predict optimal buffer layer pairing for thin film solar cell absorbers: A case study for tin sulfide/zinc oxysulfide. *Journal of Applied Physics*, **2015**, 118, 115102	2.5	24
209	Co-optimization of SnS absorber and Zn(O,S) buffer materials for improved solar cells. *Progress in Photovoltaics: Research and Applications*, **2015**, 23, 901-908	6.8	118
208	Making Record-efficiency SnS Solar Cells by Thermal Evaporation and Atomic Layer Deposition. *Journal of Visualized Experiments*, **2015**, e52705	1.6	16
207	Direct-liquid-evaporation chemical vapor deposition of smooth, highly conformal cobalt and cobalt nitride thin films. *Journal of Materials Chemistry C*, **2015**, 3, 12098-12106	7.1	14
206	Improved Cu2O-Based Solar Cells Using Atomic Layer Deposition to Control the Cu Oxidation State at the p-n Junction. *Advanced Energy Materials*, **2014**, 4, 1301916	21.8	132
205	A metal-free organic-inorganic aqueous flow battery. *Nature*, **2014**, 505, 195-8	50.4	1025

204	Impact of H2S annealing on SnS device performance **2014**,		3
203	3.88% efficient tin sulfide solar cells using congruent thermal evaporation. *Advanced Materials*, **2014**, 26, 7488-92	24	195
202	Atomic layer deposited gallium oxide buffer layer enables 1.2 V open-circuit voltage in cuprous oxide solar cells. *Advanced Materials*, **2014**, 26, 4704-10	24	205
201	Synthesis of N-Heterocyclic Stannylene (Sn(II)) and Germylene (Ge(II)) and a Sn(II) Amidinate and Their Application as Precursors for Atomic Layer Deposition. *Chemistry of Materials*, **2014**, 26, 3065-3073	9.6	49
200	Overcoming Efficiency Limitations of SnS-Based Solar Cells. *Advanced Energy Materials*, **2014**, 4, 1400496	21.8	422
199	Band offsets of n-type electron-selective contacts on cuprous oxide (Cu2O) for photovoltaics. *Applied Physics Letters*, **2014**, 105, 263901	3.4	78
198	Atomic layer deposition of Al-incorporated Zn(O,S) thin films with tunable electrical properties. *Applied Physics Letters*, **2014**, 105, 202101	3.4	17
197	X-ray absorption spectroscopy elucidates the impact of structural disorder on electron mobility in amorphous zinc-tin-oxide thin films. *Applied Physics Letters*, **2014**, 104, 242113	3.4	15
196	ALD Precursors and Reaction Mechanisms **2014**, 15-46		21
195	A path to 10% efficiency for tin sulfide devices **2014**,		8
194	Band alignment of SnS/Zn(O,S) heterojunctions in SnS thin film solar cells. *Applied Physics Letters*, **2013**, 103, 181904	3.4	68
193	Nitrogen-doped cuprous oxide as a p-type hole-transporting layer in thin-film solar cells. *Journal of Materials Chemistry A*, **2013**, 1, 15416	13	95
192	Origin of the self-limited electron densities at Al□/SrTiO□ heterostructures grown by atomic layer deposition - oxygen diffusion model. *Nanoscale*, **2013**, 5, 8940-4	7.7	19
191	Variability Improvement by Interface Passivation and EOT Scaling of InGaAs Nanowire MOSFETs. *IEEE Electron Device Letters*, **2013**, 34, 608-610	4.4	12
190	Enhancing the efficiency of SnS solar cells via band-offset engineering with a zinc oxysulfide buffer layer. *Applied Physics Letters*, **2013**, 102, 053901	3.4	245
189	Ultrathin amorphous zinc-tin-oxide buffer layer for enhancing heterojunction interface quality in metal-oxide solar cells. *Energy and Environmental Science*, **2013**, 6, 2112	35.4	150
188	Heteroepitaxy of La2O3 and La(2-x)Y(x)O3 on GaAs (111)A by atomic layer deposition: achieving low interface trap density. *Nano Letters*, **2013**, 13, 594-9	11.5	67
187	High-Quality Epitaxy of Ruthenium Dioxide, RuO2, on Rutile Titanium Dioxide, TiO2, by Pulsed Chemical Vapor Deposition. *Crystal Growth and Design*, **2013**, 13, 1316-1321	3.5	16

186	Effects of forming gas anneal on ultrathin InGaAs nanowire metal-oxide-semiconductor field-effect transistors. *Applied Physics Letters*, **2013**, 102, 093505	3.4	21
185	Atomic layer deposition of Zn(O,S) thin films with tunable electrical properties by oxygen annealing. *Applied Physics Letters*, **2013**, 102, 132110	3.4	37
184	Smooth, Low-Resistance, Pinhole-Free, Conformal Ruthenium Films by Pulsed Chemical Vapor Deposition. *ECS Journal of Solid State Science and Technology*, **2013**, 2, N41-N44	2	13
183	Creation and control of two-dimensional electron gas using Al-based amorphous oxides/SrTiO heterostructures grown by atomic layer deposition. *Nano Letters*, **2012**, 12, 4775-83	11.5	126
182	Atomic layer deposition of tin oxide with nitric oxide as an oxidant gas. *Journal of Materials Chemistry*, **2012**, 22, 4599		38
181	Atomic layer deposited zinc tin oxide channel for amorphous oxide thin film transistors. *Applied Physics Letters*, **2012**, 101, 113507	3.4	75
180	Synthesis of vanadium dioxide thin films on conducting oxides and metal insulator transition characteristics. *Journal of Crystal Growth*, **2012**, 338, 96-102	1.6	23
179	Antimony-Doped Tin(II) Sulfide Thin Films. *Chemistry of Materials*, **2012**, 24, 4556-4562	9.6	80
178	Size-Dependent-Transport Study of $hbox{In}_{0.53} hbox{Ga}_{0.47}hbox{As}$ Gate-All-Around Nanowire MOSFETs: Impact of Quantum Confinement and Volume Inversion. *IEEE Electron Device Letters*, **2012**, 33, 967-969	4.4	44
177	Frequency response of LaAlO3/SrTiO3 all-oxide field-effect transistors. *Solid-State Electronics*, **2012**, 76, 1-4	1.7	9
176	Glass-encapsulated light harvesters: more efficient dye-sensitized solar cells by deposition of self-aligned, conformal, and self-limited silica layers. *Journal of the American Chemical Society*, **2012**, 134, 9537-40	16.4	98
175	Atomic layer deposition of Sc2O3 for passivating AlGaN/GaN high electron mobility transistor devices. *Applied Physics Letters*, **2012**, 101, 232109	3.4	36
174	Chemical Vapor Deposition of Cobalt Nitride and its Application as an Adhesion-Enhancing Layer for Advanced Copper Interconnects. *ECS Journal of Solid State Science and Technology*, **2012**, 1, N79-N84	2	27
173	Thermal chemistry of copper(I)-N,N ?-di-sec-butylacetamidinate on Cu(110) single-crystal surfaces. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2012**, 30, 01A114	2.9	27
172	Vapor Deposition of Highly Conformal Copper Seed Layers for Plating Through-Silicon Vias (TSVs). *Journal of the Electrochemical Society*, **2012**, 159, D382-D385	3.9	32
171	Atomic Layer Deposition of Tin Monosulfide Thin Films. *Advanced Energy Materials*, **2011**, 1, 1116-1125	21.8	332
170	Surface Chemistry of Copper(I) Acetamidinates in Connection with Atomic Layer Deposition (ALD) Processes. *Chemistry of Materials*, **2011**, 23, 3325-3334	9.6	73
169	(Sn,Al)Ox Films Grown by Atomic Layer Deposition. *Journal of Physical Chemistry C*, **2011**, 115, 10277-10283	4.8	24

168	Three dimensional solid-state supercapacitors from aligned single-walled carbon nanotube array templates. *Carbon*, **2011**, 49, 4890-4897	10.4	70
167	Impact of ultrathin Al2O3 barrier layer on electrical properties of LaLuO3 metal-oxide-semiconductor devices. *Applied Physics Letters*, **2011**, 98, 122907	3.4	11
166	Filling Narrow Trenches by Iodine-Catalyzed CVD of Copper and Manganese on Manganese Nitride Barrier/Adhesion Layers. *Journal of the Electrochemical Society*, **2011**, 158, D248	3.9	47
165	Formation of Nickel Silicide from Direct-Liquid-Injection Chemical-Vapor-Deposited Nickel Nitride Films. *Journal of the Electrochemical Society*, **2010**, 157, H679	3.9	13
164	Heteroepitaxy of single-crystal LaLuO3 on GaAs(111)A by atomic layer deposition. *Applied Physics Letters*, **2010**, 97, 162910	3.4	37
163	Low Temperature Epitaxial Growth of High Permittivity Rutile TiO[sub 2] on SnO[sub 2]. *Electrochemical and Solid-State Letters*, **2010**, 13, G75		22
162	Raman Characterization and Polarity Tuning of Aligned Single-Walled Carbon Nanotubes on Quartz. *Japanese Journal of Applied Physics*, **2010**, 49, 02BC02	1.4	1
161	Low Temperature Atomic Layer Deposition of Tin Oxide. *Chemistry of Materials*, **2010**, 22, 4964-4973	9.6	106
160	Direct-Liquid-Injection Chemical Vapor Deposition of Nickel Nitride Films and Their Reduction to Nickel Films. *Chemistry of Materials*, **2010**, 22, 3060-3066	9.6	57
159	Selective Chemical Vapor Deposition of Manganese Self-Aligned Capping Layer for Cu Interconnections in Microelectronics. *Journal of the Electrochemical Society*, **2010**, 157, D341	3.9	56
158	Surface and interface processes during atomic layer deposition of copper on silicon oxide. *Langmuir* , **2010**, 26, 3911-7	4	71
157	Uptake of Copper Acetamidinate ALD Precursors on Nickel Surfaces. *Chemistry of Materials*, **2010**, 22, 352-359	9.6	47
156	First-Principles Simulations of Conditions of Enhanced Adhesion Between Copper and TaN(111) Surfaces Using a Variety of Metallic Glue Materials. *Angewandte Chemie*, **2010**, 122, 152-156	3.6	2
155	First-principles simulations of conditions of enhanced adhesion between copper and TaN(111) surfaces using a variety of metallic glue materials. *Angewandte Chemie - International Edition*, **2010**, 49, 148-52	16.4	15
154	FTIR study of copper agglomeration during atomic layer deposition of copper. *Materials Research Society Symposia Proceedings*, **2009**, 1155, 1		4
153	Effects of Low Temperature O2 Treatment on the Electrical Characteristics of Amorphous LaAlO3 Films by Atomic Layer Deposition. *ECS Transactions*, **2009**, 16, 471-478	1	18
152	Atomic Layer Deposition of Ruthenium Thin Films from an Amidinate Precursor. *Chemical Vapor Deposition*, **2009**, 15, n/a-n/a		15
151	On the relative stability of cobalt- and nickel-based amidinate complexes against β-migration. *International Journal of Quantum Chemistry*, **2009**, 109, 756-763	2.1	13

150	Error bounds for quantum-mechanical perturbation theory. *International Journal of Quantum Chemistry*, **2009**, 2, 151-159	2.1	3
149	In Situ Infrared Characterization during Atomic Layer Deposition of Lanthanum Oxide. *Journal of Physical Chemistry C*, **2009**, 113, 654-660	3.8	71
148	Atomic Layer Deposition of Lanthanum-Based Ternary Oxides. *Electrochemical and Solid-State Letters*, **2009**, 12, G13		34
147	Ultrathin CVD Cu Seed Layer Formation Using Copper Oxynitride Deposition and Room Temperature Remote Hydrogen Plasma Reduction. *Journal of the Electrochemical Society*, **2008**, 155, H496	3.9	29
146	Chemical Doping of Graphene Nanoribbon Field-Effect Devices **2008**,		4
145	Externally Assembled Gate-All-Around Carbon Nanotube Field-Effect Transistor. *IEEE Electron Device Letters*, **2008**, 29, 183-185	4.4	85
144	Ab Initio Molecular Dynamics Simulation on the Aggregation of a Cu Monolayer on a WN(001) Surface. *Journal of Physical Chemistry C*, **2008**, 112, 9798-9802	3.8	13
143	Synthesis and characterization of volatile liquid cobalt amidinates. *Dalton Transactions*, **2008**, 2592-7	4.3	48
142	Oxide-encapsulated vertical germanium nanowire structures and their DC transport properties. *Nanotechnology*, **2008**, 19, 485705	3.4	9
141	Synthesis and Characterization of Ruthenium Amidinate Complexes as Precursors for Vapor Deposition. *Open Inorganic Chemistry Journal*, **2008**, 2, 11-17		11
140	Computational Study on the Relative Reactivities of Cobalt and Nickel Amidinates via β-H Migration. *Organometallics*, **2007**, 26, 2803-2805	3.8	26
139	Density Function Theory Study of Copper Agglomeration on the WN(001) Surface. *Journal of Physical Chemistry C*, **2007**, 111, 9403-9406	3.8	16
138	Error Bounds and Spectral Densities. *Advances in Chemical Physics*, **2007**, 79-99		22
137	Synthesis and Sublimation Kinetics of a Highly Volatile Asymmetric Iron(II) Amidinate. *European Journal of Inorganic Chemistry*, **2007**, 2007, 1135-1142	2.3	2
136	Atmospheric pressure chemical vapor deposition of transparent conducting films of fluorine doped zinc oxide and their application to amorphous silicon solar cells. *Journal of Materials Science*, **2007**, 42, 6388-6399	4.3	61
135	High density Ru nanocrystal deposition for nonvolatile memory applications. *Journal of Applied Physics*, **2007**, 101, 124503	2.5	58
134	Atomic layer deposition of insulating nitride interfacial layers for germanium metal oxide semiconductor field effect transistors with high-κ oxide/tungsten nitride gate stacks. *Applied Physics Letters*, **2007**, 90, 212104	3.4	53
133	In-situ FTIR Study of Atomic Layer Deposition (ALD) of Copper Metal Films. *ECS Transactions*, **2007**, 11, 91-101	1	24

132	Vapor Deposition of Ruthenium from an Amidinate Precursor. *Journal of the Electrochemical Society* , **2007**, 154, D642	3.9	75
131	Atomic Layer Deposition of Praseodymium Aluminum Oxide for Electrical Applications. *Chemical Vapor Deposition*, **2006**, 12, 152-157		26
130	Thin, Continuous, and Conformal Copper Films by Reduction of Atomic Layer Deposited Copper Nitride. *Chemical Vapor Deposition*, **2006**, 12, 435-441		57
129	ALD of Scandium Oxide from Scandium Tris(N,N[sup ?]-diisopropylacetamidinate) and Water. *Electrochemical and Solid-State Letters*, **2006**, 9, F45		28
128	Atomic layer deposition of gadolinium scandate films with high dielectric constant and low leakage current. *Applied Physics Letters*, **2006**, 89, 133512	3.4	51
127	Atomic Layer Deposition of Ultrathin Copper Metal Films from a Liquid Copper(I) Amidinate Precursor. *Journal of the Electrochemical Society*, **2006**, 153, C787	3.9	180
126	Atomic layer deposition on suspended single-walled carbon nanotubes via gas-phase noncovalent functionalization. *Nano Letters*, **2006**, 6, 699-703	11.5	200
125	Atomic Layer Deposition of Y2O3Thin Films from Yttrium Tris(N,N□diisopropylacetamidinate) and Water. *Chemistry of Materials*, **2005**, 17, 4808-4814	9.6	115
124	Tantalum(V) nitride inverse opals as photonic structures for visible wavelengths. *Journal of Physical Chemistry B*, **2005**, 109, 3764-71	3.4	53
123	High performance n-type carbon nanotube field-effect transistors with chemically doped contacts. *Nano Letters*, **2005**, 5, 345-8	11.5	379
122	Synthesis and characterization of copper(I) amidinates as precursors for atomic layer deposition (ALD) of copper metal. *Inorganic Chemistry*, **2005**, 44, 1728-35	5.1	142
121	Self-aligned 40-nm channel carbon nanotube field-effect transistors with subthreshold swings down to 70 mV/decade **2005**,		1
120	ALD of High-□Dielectrics on Suspended Functionalized SWNTs. *Electrochemical and Solid-State Letters*, **2005**, 8, G89		60
119	Nucleation and Adhesion of ALD Copper on Cobalt Adhesion Layers and Tungsten Nitride Diffusion Barriers. *Electrochemical and Solid-State Letters*, **2005**, 8, G182		93
118	ALD of Hafnium Oxide Thin Films from Tetrakis(ethylmethylamino)hafnium and Ozone. *Journal of the Electrochemical Society*, **2005**, 152, G213	3.9	153
117	Determination of energy barrier profiles for high-k dielectric materials utilizing bias-dependent internal photoemission. *Applied Physics Letters*, **2004**, 85, 4133-4135	3.4	16
116	Atomic layer deposition of lanthanum aluminum oxide nano-laminates for electrical applications. *Applied Physics Letters*, **2004**, 84, 3957-3959	3.4	77
115	Surface chemistry and electrical properties of germanium nanowires. *Journal of the American Chemical Society*, **2004**, 126, 11602-11	16.4	301

114	Self-Aligned Ballistic Molecular Transistors and Electrically Parallel Nanotube Arrays. *Nano Letters*, **2004**, 4, 1319-1322	11.5	435
113	Atomic Layer Deposition to Fine-Tune the Surface Properties and Diameters of Fabricated Nanopores. *Nano Letters*, **2004**, 4, 1333-1337	11.5	352
112	Atomic Layer Deposition of Insulating Hafnium and Zirconium Nitrides. *Chemistry of Materials*, **2004**, 16, 3497-3501	9.6	83
111	Sealing Porous Low-k Dielectrics with Silica. *Electrochemical and Solid-State Letters*, **2004**, 7, G306		43
110	Carbon Nanotube Field-Effect Transistors with Integrated Ohmic Contacts and High-□Gate Dielectrics. *Nano Letters*, **2004**, 4, 447-450	11.5	430
109	Surface morphology and crystallinity control in the atomic layer deposition (ALD) of hafnium and zirconium oxide thin films. *Journal of Crystal Growth*, **2003**, 249, 251-261	1.6	233
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